

# Amir Dastgheib-Shirazi

## List of Publications by Year in descending order

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14  
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1372567

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docs citations

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times ranked

359  
citing authors

#	ARTICLE	IF	CITATIONS
1	Role of thermal SiO <sub>2</sub> on passivation of highly doped layer. AIP Conference Proceedings, 2019, , .	0.4	0
2	A novel approach for the evaluation of a phosphorus diffusion design of experiment. AIP Conference Proceedings, 2019, , .	0.4	0
3	Electrically-inactive phosphorus re-distribution during low temperature annealing. Journal of Applied Physics, 2018, 123, 161535.	2.5	3
4	Impact of Extended Contact Cofiring on Multicrystalline Silicon Solar Cell Parameters. IEEE Journal of Photovoltaics, 2017, 7, 91-96.	2.5	17
5	Optimizing phosphorus diffusion for photovoltaic applications: Peak doping, inactive phosphorus, gettering, and contact formation. Journal of Applied Physics, 2016, 119, .	2.5	45
6	Enhanced Oxidation of Thermally Grown SiO <sub>2</sub> Due to P Precipitates. Energy Procedia, 2016, 92, 457-465.	1.8	1
7	Dissolution of Electrically Inactive Phosphorus by Low Temperature Annealing. Energy Procedia, 2015, 77, 286-290.	1.8	9
8	A numerical simulation study of gallium-phosphide/silicon heterojunction passivated emitter and rear solar cells. Journal of Applied Physics, 2014, 115, 044508.	2.5	49
9	Heavily doped Si:P emitters of crystalline Si solar cells: recombination due to phosphorus precipitation. Physica Status Solidi - Rapid Research Letters, 2014, 8, 680-684.	2.4	36
10	Limitation of Industrial Phosphorus-diffused Emitters by SRH Recombination. Energy Procedia, 2014, 55, 115-120.	1.8	21
11	Relationships between Diffusion Parameters and Phosphorus Precipitation during the POCl <sub>3</sub> Diffusion Process. Energy Procedia, 2013, 38, 254-262.	1.8	45
12	A model for phosphosilicate glass deposition via POCl <sub>3</sub> for control of phosphorus dose in Si. Journal of Applied Physics, 2012, 112, 124912.	2.5	18
13	Analyzing emitter dopant inhomogeneities at textured Si surfaces by using 3D process and device simulations in combination with SEM imaging. , 2012, , .		8
14	Minimizing the electrical losses on the front side: Development of a selective emitter process from a single diffusion. , 2008, , .		25